FUJI ELECTRIC

6MBI 15LS-060

6 Pack IGBT
600V
15A

IGBT MODULE (L series)

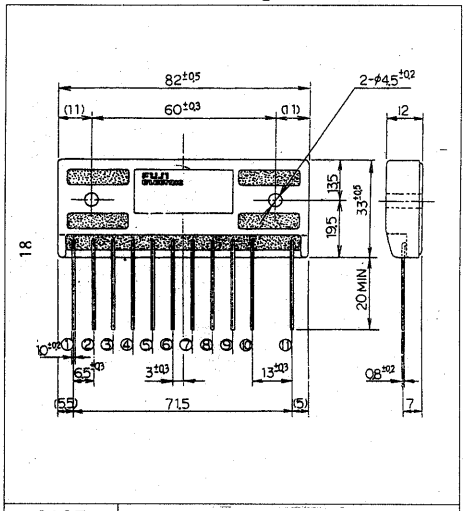
■ Features

- High Speed Switching
- Low Saturation Voltage
- Compact Package
- PCB Mounting Flexibility

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Outline Drawings



CASE	M619

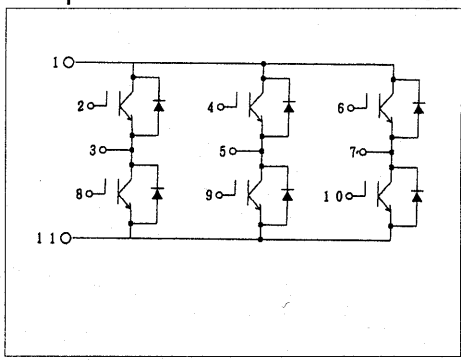
■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items		Symbols	Ratings	Units
Collecter-Emitter Voltage		V_{CES}	600	V
Gate-Emitter Voltage		V_{GES}	±20	V
Collecter Current	Continuous	I_C	15	A
	1ms	$I_{C\ pulse}$	30	
	Duty = 77%	$-I_C$	15	
	1ms	$-I_{C\ pulse}$	30	
Max. Power Dissipation		P_C	50	W
Operating Temperature		T_j	+150	°C
Storage Temperature		T_{stg}	–40 to +125	°C
Isolation Voltage	AC. 1min.	V_{is}	2000	V
Screw Torque		Mounting *1	17	kg•cm

*1 Recommendable Value 13 to 17kg•cm (M4)

■ Equilavelent Circuit Schematic

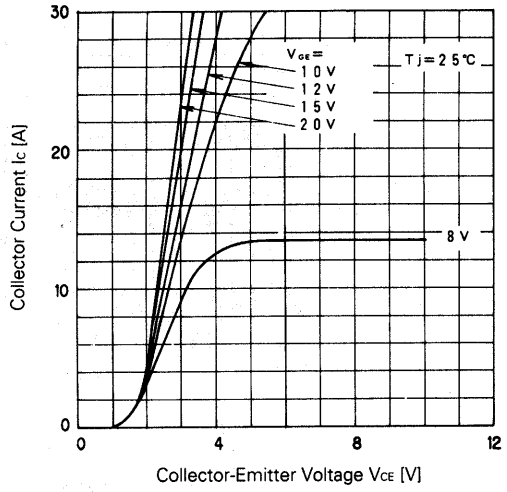


● Electrical Characteristics (Tj=25°C)

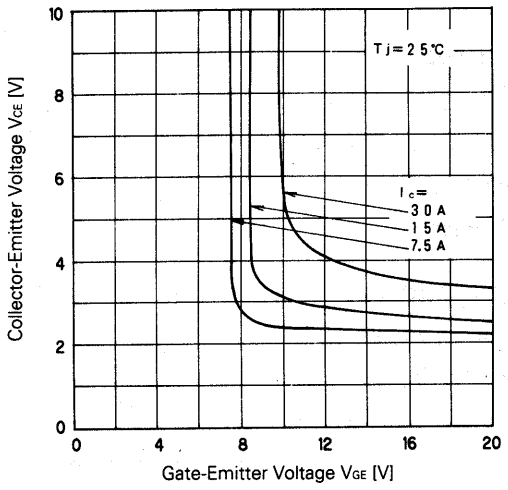
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collecter Current	I_{CES}	V_{GE}=0V V_{CE}=600V T_j=25°C			1.0	mA
Gate-Emitter Leackage Current	I_{GES}	V_{CE}=0V V_{GE}=±20V			100	nA
Gate-Emitter Threshold Voltage	$V_{GE\ (th)}$	V_{CE}=20V I_C=15mA	3.0	4.5	6.0	V
Collecter-Emitter Saturation Voltage	$V_{CE\ (sat)}$	V_{GE}=15V I_C=15A		2.7	3.5	V
Input Capacitance	C_{ies}	V_{GE}=0V		1400		pF
Output Capacitance	C_{oes}	V_{CE}=10V		–		
Reverse Transfer Capacitance	C_{res}	f=1MHz		–		
Turn-on Time	t_{on}	V_{CC}=300V		0.4	0.8	µs
	t_r	I_C=15A		0.3	0.6	
Turn-off Time	t_{off}	V_{GE}=±15V		0.6	1.0	
	t_f	R_G=150Ω		0.2	0.35	
Diode Forward On-Voltage	V_F	I_F=15A V_{GE}=0V			2.5	V
Reverse Recovery Time	t_{rr}	I_F=15A –di/dt=50A/µs V_{GE}=–10V			300	ns

● Thermal Characteristics

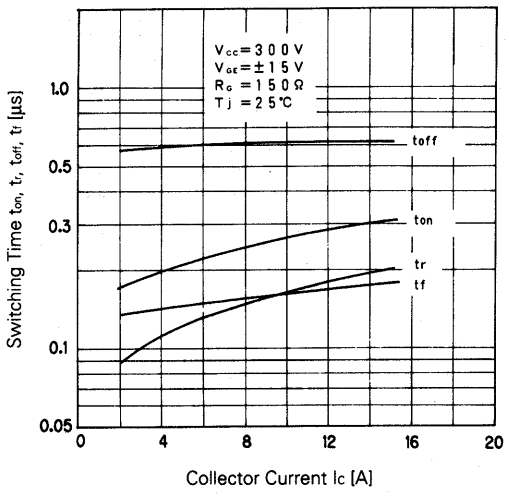
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th\ (j-c)}$	IGBT			2.5	°C/W
	$R_{th\ (j-c)}$	Diode			4.30	
	$R_{th\ (c-f)}$	With Thermal compound		0.06		



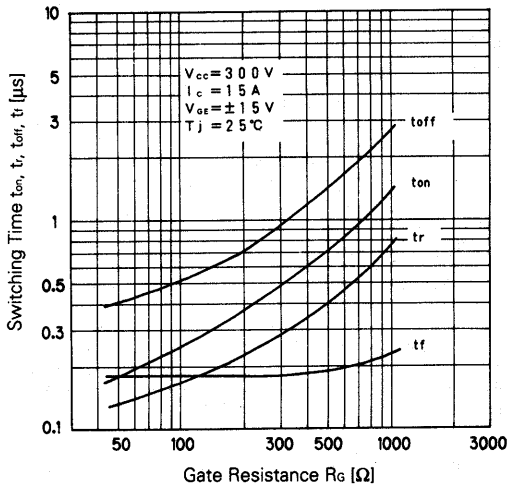
Collector Current vs. Collector-Emitter Voltage



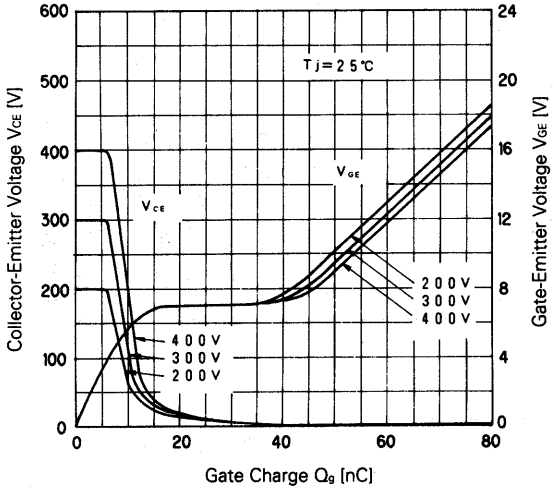
Collector-Emitter Voltage vs. Gate-Emitter Voltage



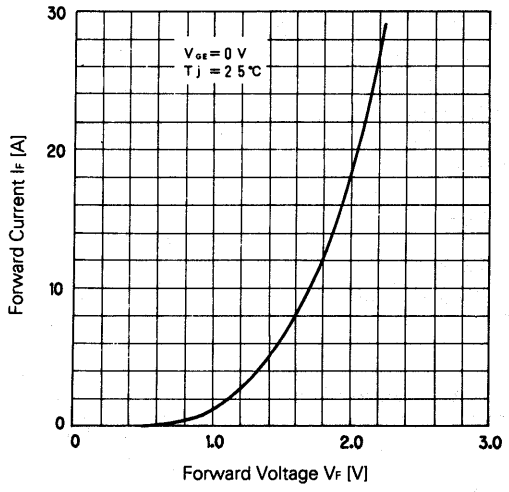
Switching Time



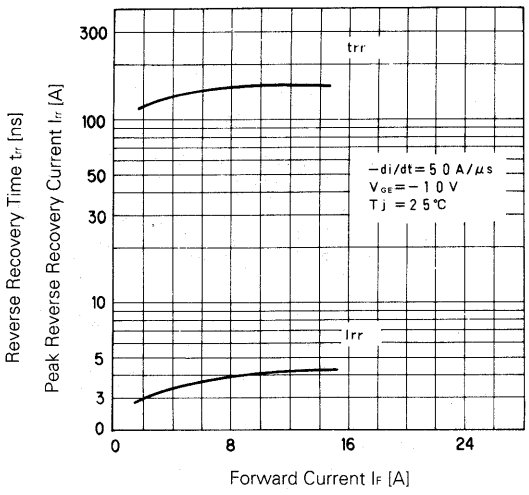
Switching Time-Gate Resistance



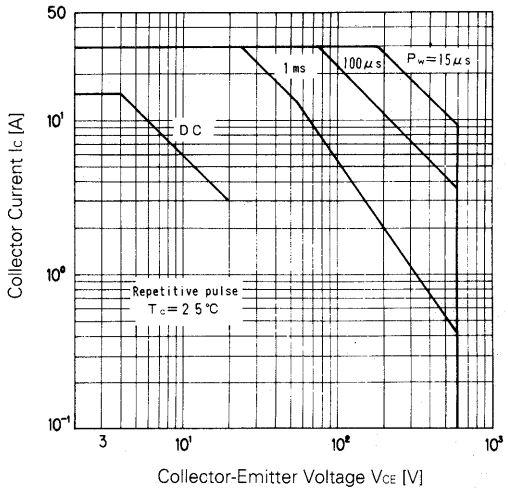
Dynamic Input Characteristic



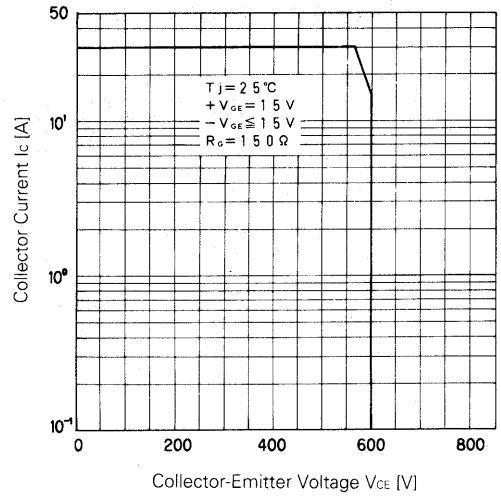
Forward Voltage of Free Wheel Diode



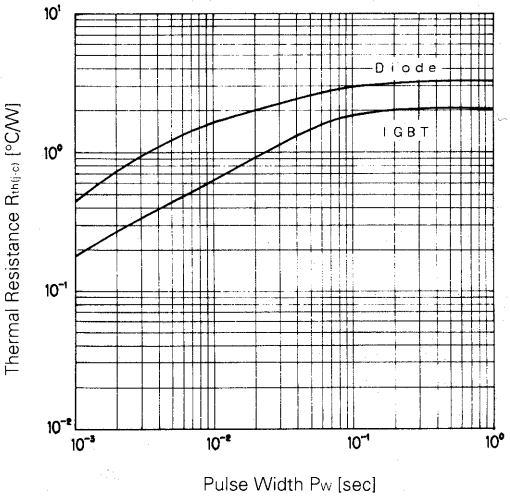
t_{rr}, I_{rr}-I_F



Safe Operating Area



Reverse Biased Safe Operating Area



Transient Thermal Resistance

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